

# BRD4N50F

Rev.A Apr.-2024

TO-252          N          MOS

N-CHANNEL MOSFET in a TO-252 Plastic Package.

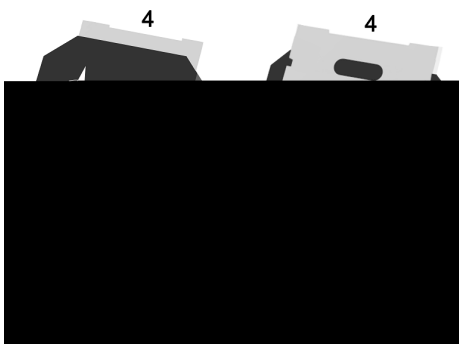
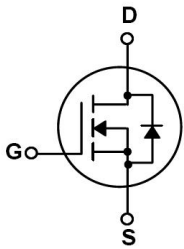
$V_{DS}=500V$        $I_D=4A$

$R_{DS(ON)}@10V$  2.2 (Typ. 1.7 )

Fast Switching.

HF Product.

These devices are well suited for power switch circuit of adaptor and charger, intergrate fast recovery diode.



PIN1 G

PIN 2 D

PIN 3 S

PIN 4 D

## / Marking

See Marking Instructions.

## / Absolute Maximum Ratings(Ta=25 )

Parameter	Symbol	Rating	Unit
Drain-Source Voltage	$V_{DSS}$	500	V
Drain Current	$I_D(T_C=25)$	4	A
Drain Current - Pulsed	$I_{DM}$	8	A
Gate-Source Voltage	$V_{GS}$	$\pm 30$	V
Single Pulsed Avalanche Energy	$E_{AS}$	176.4	mJ
Avalanche Current	$I_{AS}$	6.3	A
Power Dissipation	$P_D(T_C=25)$	50	W
Operating and Storage Temperature Range	$T_J, T_{STG}$	-55 to 150	
Junction to Ambient	$R_{JA}$	110	/W
Junction to Case	$R_{JC}$	2.5	/W

## / Electrical Characteristics(Ta=25 )

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Drain-Source Breakdown Voltage	$BV_{DSS}$	$V_{GS}=0V$ $I_D=250$ A	500			V
Zero Gate Voltage Drain Current	$I_{DSS}$	$V_{DS}=500V$ $V_{GS}=0V$			1	A
Gate-Body Leakage Current Forward	$I_{GSS}$	$V_{GS}=\pm 30V$ $V_{DS}=0V$			$\pm 100$	nA
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$ $I_D=250$ A	2.0		4.0	V
Static Drain-Source On-Resistance	$R_{DS(on)}$	$V_{GS}=10V$ $I_D=2.0A$		1.7	2.2	
Drain-Source Diode Forward Voltage	$V_{SD}$	$V_{GS}=0$ V $I_S=1.0A$			1.4	V
Input Capacitance	$C_{iss}$	$V_{DS}=25V$ $V_{GS}=0V$ $f=1.0MHz$		350		pF
Output Capacitance	$C_{oss}$			145		
Reverse Transfer Capacitance	$C_{rss}$			5		
Total Gate Charge	$Q_G$	$V_{DS}=400V$ $I_D=4.0A$ $V_{GS}=10V$		8.5		nC
Gate-Source Charge	$Q_{GS}$			3.2		
Gate-Drain Charge	$Q_{GD}$			1.5		

## / Electrical Characteristics(Ta=25 )

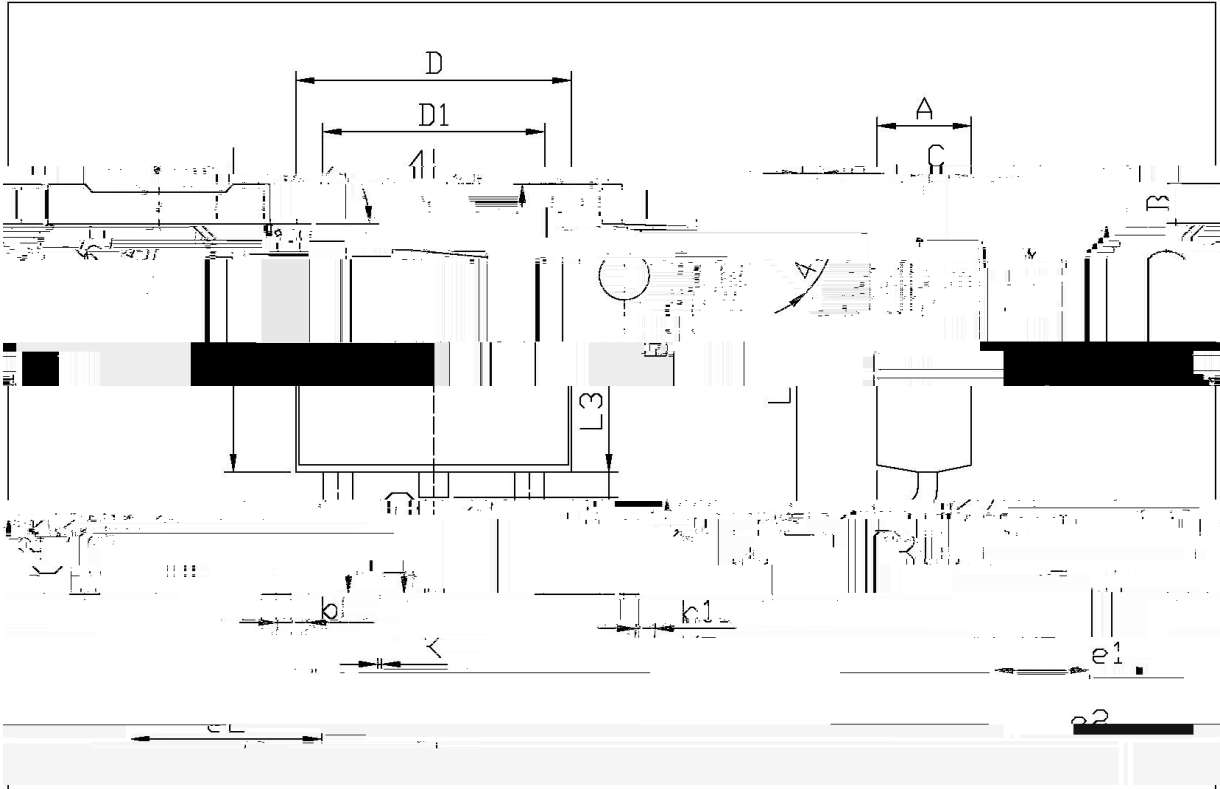
Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Turn-On Delay Time	$t_{d(on)}$	$V_{DD}=100V$ $I_D=4.0A$ $V_{GS}=10V$ $R_G=25$		4.3		ns
Turn-On Rise Time	$t_r$			17.2		
Turn-Off Delay Time	$t_{d(off)}$			22		
Turn-Off Fall Time	$t_f$			23.2		
Maximum Continuous Drain-Source Diode Forward Current	$I_S$				4	A
Maximum Pulsed Drain-Source Diode Forward Current	$I_{SM}$				8	A
Reverse Recovery Time	$t_{rr}$	$V_{GS}=0V$ $I_S=5.0A$ $dI_F/dt=100 A/s$		92		ns
Reverse Recovery Charge	$Q_{rr}$			1.45		$\mu C$

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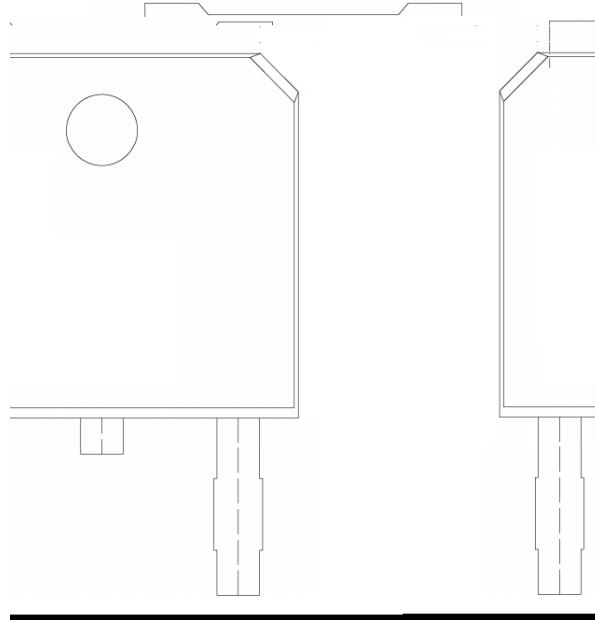
**/ Package Dimensions**



单位: mm

Dimensions in Millimeters		Dimensions in Millimeters	
Symbol	Value	Symbol	Value
Min	2.24	Min	0.95
Max	2.34	Max	1.25
Min	4.42	Min	0.70
Max	4.73	Max	0.90
Min	0.85	Min	0.25
Max	1.03	Max	0.55
Min	0.45	Min	0.60
Max	0.75	Max	0.90
Min	5.10	Min	0.00
Max	5.50	Max	0.10

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